Finding Negative Vacancy Formation Energies in Amorphous Silicon

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Introduction

• Goal: determine whether Amorphous Silicon has negative vacancy formation energies.
• Vacancies control diffusion in solids
• Vacancy formation energies
• Amorphous solids
Methodology

• Using LAMMPS software to conduct atomic simulations of amorphous silicon structures
• ADA Cluster at Texas A&M HPRC
• 20 cores with 2560 MB for between 20 and 100 Hrs.
Project Overview

1. Melt and quench simulations
2. Preliminary vacancy formation energy calculation
3. Generalized atom removal energy calculations
4. Repeated calculations for varied simulation size
5. Self Interstitial formation energy calculations
Results

• Vacancy Formation Energy Histograms

Performing algorithm on a-Si structures of 1000 atoms cooled at rates of $10^{10}$ and $10^{12}$K/s.
Results

- Atom removal Energy vs Atom Cohesion Energy
Results

- ARE calculations for varied sizes
Results

Self Interstitial formation Energies

Amorphous silicon quenched at $10^{-10}$ K/S

Crystal with one self interstitial

Amorphous silicon quenched at $10^{-12}$ K/S
Conclusion

- Found that Amorphous Silicon has negative vacancy formation energies.
- Results suggest negative vacancy formation energy is due to relaxation in structures.
- A prior experimental study shows bulk amorphous silicon continuously relaxing into a crystalline form $^1$.
- More research is required to fully understand this phenomenon.

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